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(FILE 'USPAT' ENTERED AT 12:47:30 ON 10 FEB 92)

11 44 S SEMICONDUCTOR AND HEXAGONAL AND POLYGONAL AND BASE  
12 3 S L1 AND DELAY AND CONSTANT  
13 3 S L2 AND GATE AND PAD  
14 3 S L3 AND FINGER?

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3. 4,593,302, Jun. 3, 1986, Process for manufacture of high power MOSFET  
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